

FEATURES■ **HIGH POWER**

P1dB=42.5dBm at 5.3GHz to 5.9GHz

■ **HIGH GAIN**

G1dB= 11.5dB at 5.3GHz to 5.9GHz

■ **BROAD BAND INTERNALLY MATCHED FET**■ **HERMETICALLY SEALED PACKAGE****RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset=2.8A f = 5.3 to 5.9GHz	dBm	41.5	42.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	10.5	11.5	—
Drain Current	IDS1		A	—	4.4	5.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	38	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 30.5dBm	dBc	-40	-45	—
Drain Current	IDS2	(Single Carrier Level)	A	—	—	5.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	80

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 5.2A	S	—	5.2	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 40mA	V	-1.0	-1.9	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	8.8	—
Gate-Source Breakdown Voltage	VGSO	IGS= -180μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	1.5	1.8

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